

# MA2SV04

## Silicon epitaxial planar type

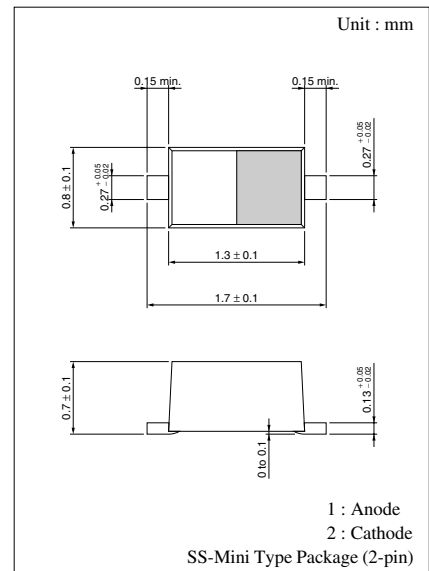
For VCO

### ■ Features

- Good linearity and large capacitance-ratio in  $C_D$ — $V_R$  relation
- Small series resistance  $r_D$
- SS-mini type package, allowing downsizing of equipment and automatic insertion through the taping package

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	6	V
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



Marking Symbol: 5

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 5\text{ V}$			10	nA
Diode capacitance	$C_{D(1V)}$	$V_R = 1\text{ V}, f = 1\text{ MHz}$	10.0		11.1	pF
	$C_{D(3V)}$	$V_R = 3\text{ V}, f = 1\text{ MHz}$	5.8		6.4	pF
Series resistance*	$r_D$	$V_R = 3\text{ V}, f = 470\text{ MHz}$			0.35	$\Omega$

Note) 1. Rated input/output frequency: 470 MHz

2. \*:  $r_D$  measuring instrument: YHP MODEL 4191A RF IMPEDANCE ANALYZER

